

# CSM620N02S23

## 60V N-Channel Enhancement Mode MOSFET – ESD Protected

Voltage

60 V

Current

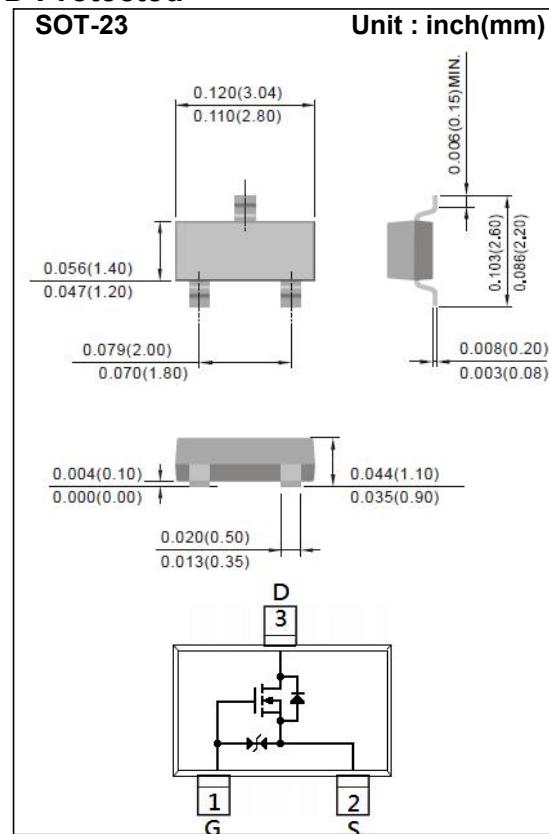
200mA

### Features

- $R_{DS(ON)}$ ,  $V_{GS}=10V$ ,  $I_D=500mA < 2.5\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}=4.5V$ ,  $I_D=200mA < 3\Omega$
- Advanced Trench Process Technology
- High Density Cell Design For Ultra Low On-Resistance
- Very Low Leakage Current In Off Condition
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc
- ESD Protected 2kV HBM
- Lead free in compliance with EU RoHS 2.0

### Mechanical Data

- Case: SOT-23 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0003 ounces, 0.0084 grams



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current (Note 4)	$I_D$	200	mA
Pulsed Drain Current (Note 1)	$I_{DM}$	2000	
Power Dissipation	$T_A=25^\circ C$	500	mW
	Derate above $25^\circ C$	4	mW/ $^\circ C$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150	$^\circ C$
Typical Thermal Resistance - Junction to Ambient (Note 3,4)	$R_{\theta JA}$	250	$^\circ C/W$

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## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=10\mu\text{A}$	60	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	-	2.5	
Drain-Source On-State Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=500\text{mA}$	-	-	2.5	$\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=200\text{mA}$	-	-	3	
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 10$	
Forward Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=250\text{mA}$	100	-	-	$\text{mS}$
<b>Dynamic</b> (Note 5)						
Total Gate Charge	$Q_g$	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=250\text{mA}, V_{\text{GS}}=5\text{V}$ (Note 1,2)	-	0.8	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	0.35	-	
Gate-Drain Charge	$Q_{\text{gd}}$		-	0.2	-	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	35	-	pF
Output Capacitance	$C_{\text{oss}}$		-	13	-	
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	8	-	
Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=30\text{V}, I_{\text{D}}=200\text{mA}, V_{\text{GS}}=10\text{V}, R_{\text{G}}=10\Omega$ (Note 1,2)	-	2.7	-	ns
Turn-On Rise Time	$t_{\text{r}}$		-	19	-	
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	15	-	
Turn-Off Fall Time	$t_{\text{f}}$		-	23	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_{\text{s}}$	---	-	-	300	$\text{mA}$
Diode Forward Voltage	$V_{\text{SD}}$	$I_{\text{s}}=200\text{mA}, V_{\text{GS}}=0\text{V}$	-	0.82	1.3	V

### NOTES:

1. Pulse width $\leq 300\text{us}$ , Duty cycle $\leq 2\%$ .
2. Essentially independent of operating temperature typical characteristics.
3.  $R_{\text{OJA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
5. Guaranteed by design, not subject to production testing.

## CSM620N02S23

### TYPICAL CHARACTERISTIC CURVES

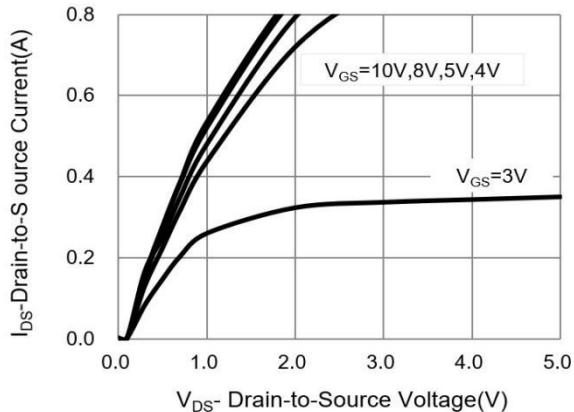


Fig.1 On-Region Characteristics

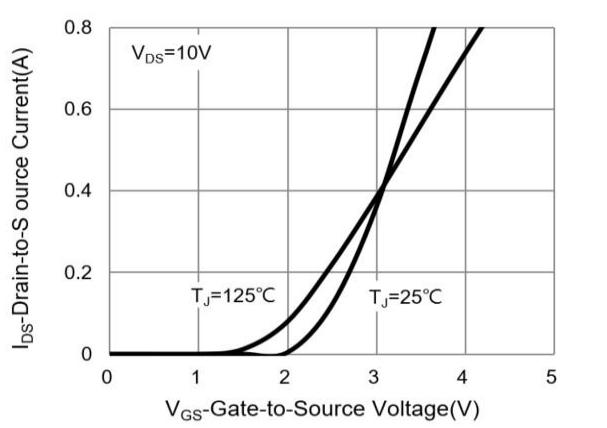


Fig.2 Transfer Characteristics

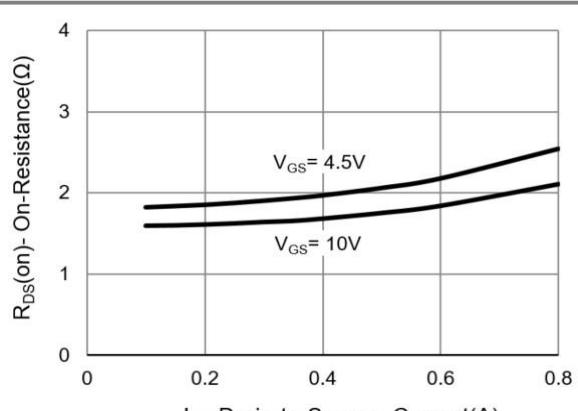


Fig.3 On-Resistance vs. Drain Current

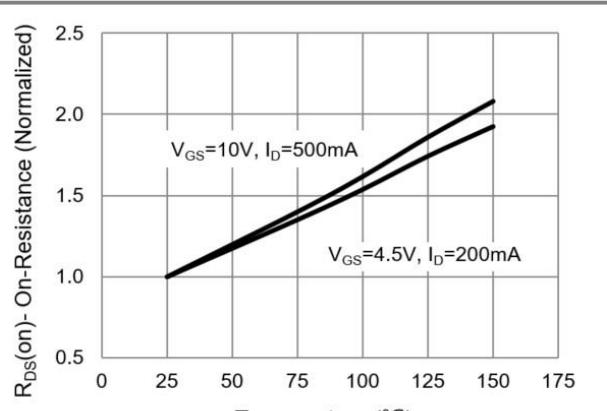


Fig.4 On-Resistance vs. Junction temperature

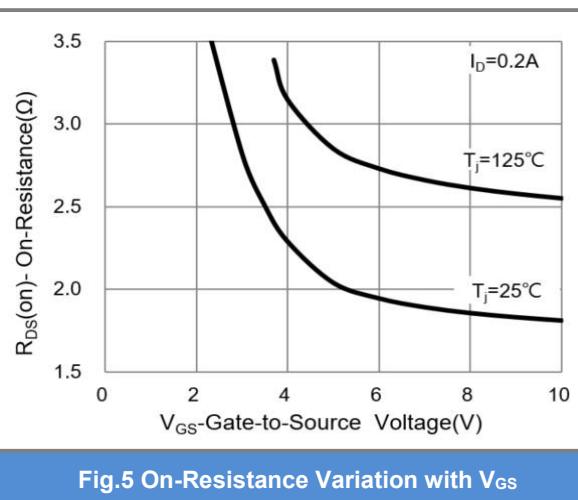


Fig.5 On-Resistance Variation with V<sub>G</sub>

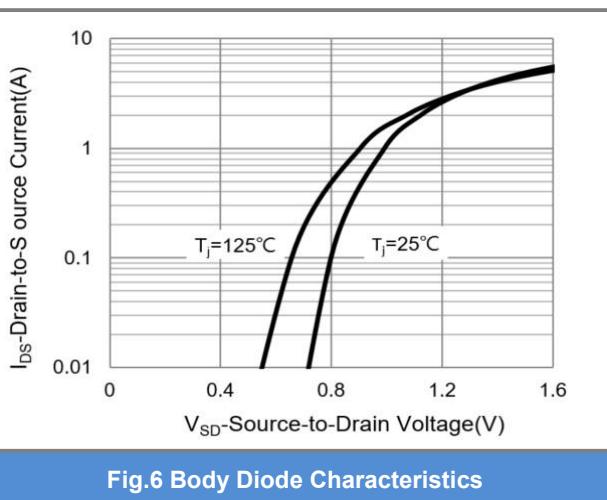


Fig.6 Body Diode Characteristics

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### TYPICAL CHARACTERISTIC CURVES

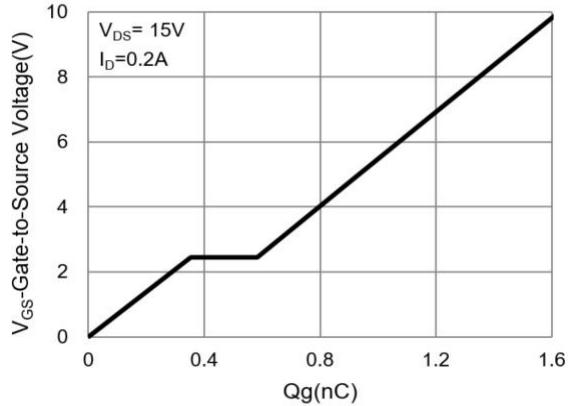


Fig.7 Gate-Charge Characteristics

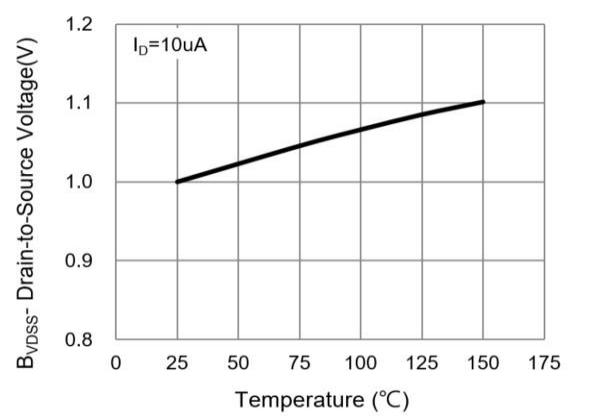


Fig.8 Breakdown Voltage Variation vs. Temperature

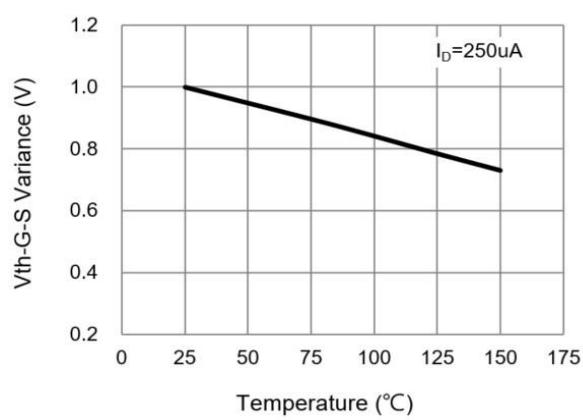


Fig.9 Threshold Voltage Variation with Temperature

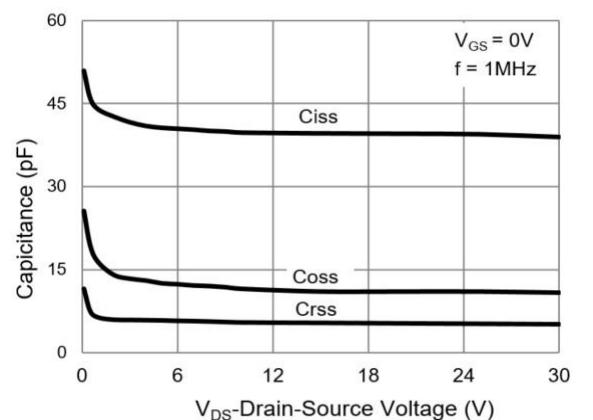
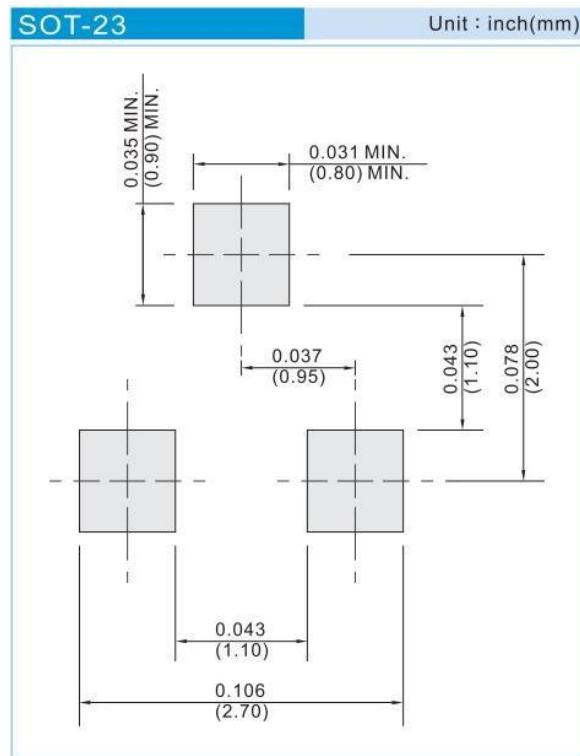


Fig.10 Capacitance vs. Drain-Source Voltage

## CSM620N02S23

### Mounting Pad Layout



## **CSM620N02S23**

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